



Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Features

- Compliant to LIN 2.0, LIN 2.1, LIN 2.2, LIN 2.2A, and ISO 17987-4 Electrical Physical Layer (EPL) Specification
- Compliant to SAE J2602 LIN Network for Vehicle Applications
- Support LIN Data Rates up to 20 Kbps
- Support Wide V_{BAT} Input Voltage Range: 4.5 V to 40 V
- Low-current Standby Mode and Sleep Mode with Bus and Local Wake-up Capability
- Input Levels Compatible with 3.3-V and 5-V MCU Interface
- $\pm 2\%$ Accuracy 5-V or 3.3-V Voltage Regulator with up to 125-mA (DFN, ESOP) Capability
- Ideal Passive Behavior to LIN Bus when Unpowered
- Integrated Pull-up Resistor for LIN Slave Applications
- Protection Feature :
 - IEC 61000-4-2 ESD Protection up to ± 15 kV
 - Bus Fault Protection: ± 45 V
 - V_{BAT} and V_{CC} Undervoltage Protection
 - Voltage Regulator Short to Ground Protection
 - TXD Dominant Time-out Function
 - Thermal Shutdown Protection
- Available in SOP8 Package, ESOP8 Package, and Leadless DFN3X3-8 Package with Improved Automated Optical Inspection (AOI) Capability
- AEC-Q100 Qualified for Automotive Applications, Grade 1

Applications

- Automotive and Transportation
- Body Electronics / Lighting
- Power Train / Chassis
- Infotainment / Cluster
- ADAS / Safety

Description

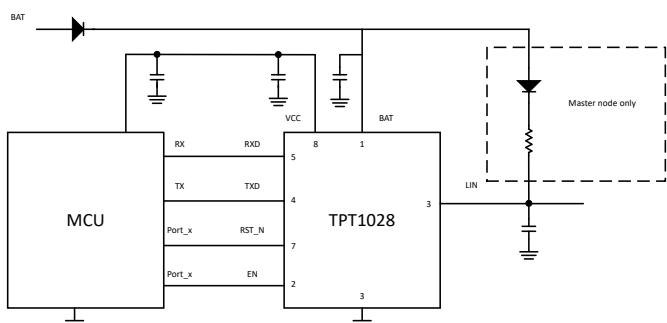
The TPT1028xQ is a local interconnect network (LIN) system basis chip (SBC), which includes a LIN transceiver, compliant to the ISO 17987-4, SAE J2602 and LIN 2.0, LIN 2.1, LIN 2.2, and LIN 2.2-A physical layer standard, and an integrated low drop out (LDO) voltage regulator. LIN is a low-speed Universal Asynchronous Receiver Transmitter (UART) communication protocol that supports automotive in-vehicle sub-networks.

The LIN SBC is designed in LIN networks up to 20 Kbps and reduces system complexity by providing a 5-V or 3.3-V LDO to power microprocessors, sensors, and other devices. The device supports Sleep mode, in which the LDO and LIN transceivers are shut down while still able to be woken up via the LIN bus. The device integrates a pull high resistor for LIN slave applications and ESD protection, which allows applications to operate with a reduced dependence on external components. With an optimized circuit design, the TPT1028xQ exhibits very low electromagnetic emission (EME) and high electromagnetic immunity (EMI) capabilities.

As designed, the device features overvoltage and loss of ground protection from -45 V to $+45$ V, over-temperature shutdown, under voltage and short to ground protections, and other protection features to enhance the device and network robustness.

The TPT1028xQ is available in SOP-8, ESOP-8, and DFN3X3-8 packages and is AEC-Q100 qualified for automotive applications.

Typical Application Circuit



Automotive Fault Protected 125mA LIN System Basis Chip (SBC)**Table of Contents**

Features.....	1
Applications.....	1
Description.....	1
Typical Application Circuit.....	1
Product Family Table.....	3
Revision History.....	3
Pin Configuration and Functions.....	4
Specifications.....	5
Absolute Maximum Ratings ⁽¹⁾	5
ESD (Electrostatic Discharge Protection).....	5
Recommended Operating Conditions.....	6
Thermal Information.....	6
Electrical Characteristics.....	7
Duty Cycles.....	10
AC Timing Requirements.....	11
Parameter Measurement Information.....	12
Test Circuit.....	12
Parameter Diagram.....	12
Detailed Description.....	14
Overview.....	14
Functional Block Diagram.....	14
Feature Description.....	14
Device Operating Modes.....	14
Power Supply.....	16
Protection Features.....	17
Application and Implementation.....	18
Typical Application.....	18
Tape and Reel Information.....	19
Package Outline Dimensions.....	20
DFN3X3-8.....	20
SOP8.....	21
ESOP8.....	22
Order Information.....	23
IMPORTANT NOTICE AND DISCLAIMER.....	24



TPT1028xQ

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Product Family Table

Order Number	VCC (V)	ICC (mA)	Bus Fault Protection (V)	Package
TPT10283Q-DFCR-S	3.3	125	45	DFN3X3-8
TPT10283Q-SO1R-S	3.3	100	45	SOP-8
TPT10283Q-ES1R-S	3.3	125	45	ESOP-8
TPT10285Q-DFCR-S	5	125	45	DFN3X3-8
TPT10285Q-SO1R-S	5	100	45	SOP-8
TPT10285Q-ES1R-S	5	125	45	ESOP-8

Revision History

Date	Revision	Notes
2022-12-05	Rev.P.0	Initial version
2024-11-30	Rev.A.0	Released version

Pin Configuration and Functions

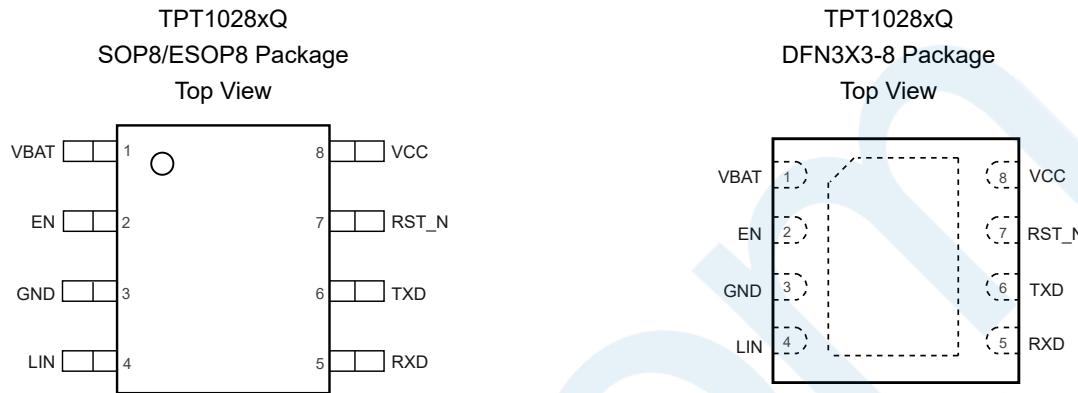


Table 1. Pin Functions: TPT1028xQ

Pin		I/O	Description
No.	Name		
1	VBAT	HV Power Input	High voltage power supply from the battery
2	EN	Input	Enable input
3	GND	GND	Ground
4	LIN	HV I/O	LIN bus input/output line
5	RXD	Output	LIN receive data output
6	TXD	Input	LIN transmit data input
7	RST_N	Output	Reset output (active low)
8	VCC	Power Output	Integrated voltage regulator output

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Specifications

Absolute Maximum Ratings (1)

Parameter		Conditions	Min	Max	Unit
V_{BAT}	Battery Supply Voltage Range		-0.3	45	V
V_{CC}	Pin VCC Voltage Range		-0.3	7	V
V_{TXD}	Pin TXD Voltage Range		-0.3	$V_{CC} + 0.3$	V
V_{RXD}	Pin RXD Voltage Range		-0.3	$V_{CC} + 0.3$	V
V_{RST_N}	Pin RST_N Voltage Range		-0.3	$V_{CC} + 0.3$	V
V_{EN}	Pin EN Voltage Range	$I_{EN} < 500 \mu A$	-0.3	$V_{CC} + 0.3$	V
V_{LIN}	Pin LIN Voltage Range	With respect to GND, V_{BAT} , and V_{EN}	-45	45	V
T_J	Junction Temperature (2)		-55	150	°C
T_{STG}	Storage Temperature		-55	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

(2) This data was taken with the JEDEC standard multilayer test boards.

ESD (Electrostatic Discharge Protection)

Parameter		Condition	Mini	Typ	Max	Unit
V_{ESD}	Electrostatics Discharge (1)(2)	IEC61000-4-2(150 pF, 330 Ω discharge circuit), contact discharge on LIN bus pins	-15	-	15	kV
		Human Body Model (HBM) on LIN bus pins	-15	-	15	kV
		Human Body Model (HBM) on any other pins	-6	-	6	kV
		Charged Device Model (CDM) on all pins	-750	-	750	V
V_{TRAN}	Transient Immunity ISO 7637-2 on Bus Pins	Pulse1	-100	-	-	V
		Pulse2a	-	-	75	V
		Pulse3a	-150	-	-	V
		Pulse3b	-	-	100	V



TPT1028xQ

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Recommended Operating Conditions

	Parameter	Min	Max	Unit
V_{BAT}	Battery Power Supply	5.5	40	V
V_{LIN}	LIN Bus Input Voltage	0	40	V
V_{LOGIC}	Logic Pin Voltage	0	5.25	V
T_J	Operating Virtual Junction Temperature Range	-40	150	°C

Thermal Information

Package Type	θ_{JA}	θ_{JC}	Unit
SOP8	114.82	47.81	°C/W
DFN3x3-8	40.41	53.02	°C/W
ESOP8	32.88	45.13	°C/W

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)
Electrical Characteristics

All test conditions: $V_{BAT} = 5.5$ V to 40 V, $R_L = 500 \Omega$, $T_A = -40^\circ\text{C}$ to 125°C , unless otherwise noted.

Parameter	Conditions	Min	Typ	Max	Unit	
Pin V_{BAT}						
V_{BAT}	Supply Voltage	5.5		40	V	
$V_{TH_DET_PON}$	Power-on Detection Threshold	3.4	3.9	4.4	V	
$V_{TH_DET_POFF}$	Power-off Detection Threshold	3	3.5	4	V	
$V_{HYS_DET_PON}$	Hysteresis Voltage on Power-on Detection ⁽¹⁾	50	300		mV	
I_{BAT}	Standby Mode Supply Current	$V_{LIN} = V_{BAT}$	25	75	μA	
	Sleep Mode Supply Current	$V_{LIN} = V_{BAT} = 12$ V	7.8	23	μA	
		$V_{LIN} = V_{BAT}$	12	50	μA	
	Normal Mode Supply Current	Recessive; $V_{LIN} = V_{BAT}$; $V_{RXD} = V_{CC}$; $V_{RST_N} = \text{High}$		167	300	μA
		Dominant; $V_{LIN} = V_{BAT}$; $V_{RXD} = 0$ V; $V_{RST_N} = \text{High}$		1.6	6.5	mA
Pin V_{CC}						
V_{CC}	Supply Voltage	$14 \text{ V} > V_{BAT} > 6 \text{ V}$; $V_{CC} = 5 \text{ V}$; $I_{CC} = -125 \text{ mA}$ to 0 mA (DFN and ESOP); $I_{CC} = -100 \text{ mA}$ to 0 mA (SOP)	4.9	5	5.1	V
V_{CC}	Supply Voltage	$14 \text{ V} > V_{BAT} > 4.5 \text{ V}$; $V_{CC} = 3.3 \text{ V}$; $I_{CC} = -125 \text{ mA}$ to 0 mA (DFN and ESOP); $I_{CC} = -100 \text{ mA}$ to 0 mA (SOP)	3.234	3.3	3.366	V
ΔV_{CC_LINE}	Line Regulation	$I_{CC} = 10 \text{ mA}$		50	mV	
ΔV_{CC_LOAD}	Load Regulation	$I_{CC} = 1$ to 100 mA; $V_{BAT} = 14$ V		40	mV	
V_{DROP}	Dropout Voltage	$V_{DROP} = V_{BAT} - V_{CC}$; $I_{CC} = 100 \text{ mA}$; $V_{CC} = 5 \text{ V}$ version		300	600	mV
I_{O_LIMIT}	Output Current Limit	V_{CC} short to ground		310	mA	
V_{UVD}	Undervoltage Detection Voltage	$V_{CC} = 5 \text{ V}$	3.6	4.55	4.6	V
V_{UVD}	Undervoltage Detection Voltage ⁽¹⁾	$V_{CC} = 3.3 \text{ V}$	2.7	2.9	3.0	V
V_{UVR}	Undervoltage Recovery Voltage	$V_{CC} = 5 \text{ V}$	4.0	4.25	4.9	V
V_{UVR}	Undervoltage Recovery Voltage ⁽¹⁾	$V_{CC} = 3.3 \text{ V}$	2.9	2.75	3.1	V
$R_{VBAT-VCC}$	Resistance between Pin V_{BAT} and V_{CC} ⁽¹⁾	$V_{CC} = 5 \text{ V}$, $V_{BAT} = 4.5 \text{ V}$ to 5.5 V; $I_{CC} = 5 \text{ mA}$ to 70 mA, $T_j = 85^\circ\text{C}$		4	Ω	

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Parameter		Conditions	Min	Typ	Max	Unit
R _{V_{BAT}-V_{CC}}	Resistance between Pin V _{BAT} and V _{CC} ⁽¹⁾	V _{CC} = 5 V, V _{BAT} = 4.5V to 5.5V; I _{CC} = 5 mA to 70 mA, T _j = 150°C			5	Ω
C _O	Output Capacitance ⁽¹⁾	Equivalent series resistance < 2 Ω	1	10	-	μF
PSRR	Power Supply Rejection Ratio ⁽¹⁾	V _{AC} = 0.5 V _{P-P} , I _{CC} = 10 mA , f = 100 Hz , C _{OUT} = 10 μF	-	85		dB
Pin TXD						
V _{IH}	High-level Input Voltage	2.97 V < V _{CC} < 5.5 V	0.7 x V _{CC}			V
V _{IL}	Low-level Input Voltage	2.97 V < V _{CC} < 5.5 V			0.3 x V _{CC}	V
V _{HYS_TXD}	Hysteresis Voltage on Pin TXD		200			mV
R _{PU_TXD}	Pin TXD Pull-up Resistance		250	350	500	kΩ
Pin RXD						
I _{OH}	High-level Output Current	Normal mode; V _{LIN} = V _{BAT} , V _{RXD} = V _{CC} - 0.4 V			-0.4	mA
I _{OL}	Low-level Output Current	Normal mode; V _{LIN} = 0 V, V _{RXD} = 0.4 V	0.4			mA
Pin EN						
V _{IH}	High-level Input Voltage		2			V
V _{IL}	Low-level Input Voltage				0.8	V
R _{PD}	Pull-down Resistance		250	350	500	kΩ
Pin RST_N						
R _{PU}	Pull-up Resistance	V _{RST_N} = V _{CC} - 0.4 V; V _{CC} = 2.97 V to 5.5 V	3	5.5	12	kΩ
I _{OL}	Low-level Output Current	V _{RST_N} = 0.4 V; V _{CC} = 2.97 V to 5.5 V;	2.5			mA
V _{OL}	Low-level Output Voltage	V _{RST_N} = 0.4 V; V _{CC} = 2.97 V to 5.5 V;			0.8	V
V _{OH}	High-level Output Voltage		0.8 x V _{CC}		V _{CC} + 0.3	V
Pin LIN						
I _{BUS_LIM}	Dominant Output Current Limiation	V _{BAT} = V _{LIN} = 18 V; V _{TXD} = 0 V	40	135	200	mA
R _{PU}	Pull-up Resistance	Sleep mode; V _{SLP_N} = 0 V	50	150	250	kΩ
I _{BUS_REC}	Recevier Recessive Input Leakage Current	V _{BAT} = 5.5 V; V _{LIN} = 18 V; V _{TXD} = 5 V			20	μA
I _{BUS_DOM}	Recevier Dominant Input Leakage Current	Normal mode; V _{BAT} = 12 V; V _{LIN} = 0 V; V _{TXD} = 5 V	-500			μA

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Parameter		Conditions	Min	Typ	Max	Unit
V_{SerDiode}	Voltage Drop at the Serial Diode ⁽¹⁾	Pull-up path with R_{SLAVE} ; $I_{\text{SerDiode}} = 10 \mu\text{A}$	0.4		1	V
$I_{\text{BUS_NO_GND}}$	Ground Loss Bus Current	$V_{\text{BAT}} = 40 \text{ V}$; $V_{\text{LIN}} = 0 \text{ V}$	-850		10	μA
$I_{\text{BUS_NO_BAT}}$	Battery Loss Bus Current	$V_{\text{BAT}} = 0 \text{ V}$; $V_{\text{LIN}} = 40 \text{ V}$			20	μA
$V_{\text{BUS_PAS_DOM}}$	Receiver Dominant				$0.4 \times V_{\text{BAT}}$	V
$V_{\text{BUS_PAS_REC}}$	Receiver Recessive		$0.6 \times V_{\text{BAT}}$			V
$V_{\text{BUS_CNT}}$	Receiver Center Voltage		$0.475 \times V_{\text{BAT}}$	$0.5 \times V_{\text{BAT}}$	$0.525 \times V_{\text{BAT}}$	V
V_{HYS}	Receiver Hysteresis Voltage		$0.05 \times V_{\text{BAT}}$	$0.15 \times V_{\text{BAT}}$	$0.175 \times V_{\text{BAT}}$	V
R_{SLAVE}	Slave Resistance	Between LIN and V_{BAT} ; $V_{\text{BAT}} = 12 \text{ V}$; $V_{\text{LIN}} = 0 \text{ V}$	20	30	60	$\text{k}\Omega$
C_{LIN}	Pin LIN Capacitance ⁽¹⁾				30	pF
$V_{\text{O_DOM}}$	Dominant Output Voltage	Normal mode; $V_{\text{TXD}} = 0 \text{ V}$			$0.2 \times V_{\text{BAT}}$	V
$V_{\text{O_REC}}$	Recessive Output Voltage	Normal mode; $V_{\text{TXD}} = V_{\text{cc}}$	$0.85 \times V_{\text{BAT}}$			V
Thermal shutdown						
$T_{\text{J_SD}}$	Shutdown Junction Temperature ⁽¹⁾		165	175	185	°C
$T_{\text{J_SD_HYS}}$	Thermal Shutdown Hysteresis ⁽¹⁾			20		°C

(1) The data is based on bench tests and design simulation.

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Duty Cycles

All test conditions: $V_{BAT} = 5.5 \text{ V}$ to 40 V , $R_L = 500 \Omega$, $T_A = -40^\circ\text{C}$ to 125°C , see [Figure 2](#), unless otherwise noted.

Parameter	Conditions	Min	Typ	Max	Unit
D1 Duty cycle 1; $D1 = t_{BUS_REC_MIN} / 2 \times t_{BIT}$	$V_{TH_REC_MAX} = 0.744 \times V_{BAT}$; $V_{TH_DOM_MAX} = 0.581 \times V_{BAT}$; 20 kbps; $t_{BIT} = 50 \mu\text{s}$; $7 \text{ V} \leq V_{BAT} \leq 40 \text{ V}$	0.396			
D1 Duty cycle 1; $D1 = t_{BUS_REC_MIN} / 2 \times t_{BIT}$	$V_{TH_REC_MAX} = 0.744 \times V_{BAT}$; $V_{TH_DOM_MAX} = 0.581 \times V_{BAT}$; 20 kbps; $t_{BIT} = 50 \mu\text{s}$; $5.5 \text{ V} \leq V_{BAT} < 7 \text{ V}$	0.396			
D2 Duty cycle 2; $D2 = t_{BUS_REC_MAX} / 2 \times t_{BIT}$	$V_{TH_REC_MIN} = 0.422 \times V_{BAT}$; $V_{TH_DOM_MIN} = 0.284 \times V_{BAT}$; 20 kbps; $t_{BIT} = 50 \mu\text{s}$; $7.6 \text{ V} \leq V_{BAT} \leq 40 \text{ V}$			0.581	
D2 Duty cycle 2; $D2 = t_{BUS_REC_MAX} / 2 \times t_{BIT}$	$V_{TH_REC_MIN} = 0.464 \times V_{BAT}$; $V_{TH_DOM_MIN} = 0.312 \times V_{BAT}$; 20 kbps; $t_{BIT} = 50 \mu\text{s}$; $5.5 \text{ V} \leq V_{BAT} < 7.6 \text{ V}$			0.581	
D3 Duty cycle 3; $D3 = t_{BUS_REC_MIN} / 2 \times t_{BIT}$	$V_{TH_REC_MAX} = 0.778 \times V_{BAT}$; $V_{TH_DOM_MAX} = 0.616 \times V_{BAT}$; 10.4 kbps; $t_{BIT} = 96 \mu\text{s}$; $7 \text{ V} \leq V_{BAT} \leq 40 \text{ V}$	0.417			
D3 Duty cycle 3; $D3 = t_{BUS_REC_MIN} / 2 \times t_{BIT}$	$V_{TH_REC_MAX} = 0.778 \times V_{BAT}$; $V_{TH_DOM_MAX} = 0.616 \times V_{BAT}$; 10.4 kbps; $t_{BIT} = 96 \mu\text{s}$; $5.5 \text{ V} \leq V_{BAT} < 7 \text{ V}$	0.417			
D4 Duty cycle 4; $D4 = t_{BUS_REC_MAX} / 2 \times t_{BIT}$	$V_{TH_REC_MIN} = 0.389 \times V_{BAT}$; $V_{TH_DOM_MIN} = 0.251 \times V_{BAT}$; 10.4 kbps; $t_{BIT} = 96 \mu\text{s}$; $7.6 \text{ V} \leq V_{BAT} \leq 40 \text{ V}$			0.590	
D4 Duty cycle 4; $D4 = t_{BUS_REC_MAX} / 2 \times t_{BIT}$	$V_{TH_REC_MIN} = 0.389 \times V_{BAT}$; $V_{TH_DOM_MIN} = 0.251 \times V_{BAT}$; 10.4 kbps; $t_{BIT} = 96 \mu\text{s}$; $5.5 \text{ V} \leq V_{BAT} < 7.6 \text{ V}$			0.590	

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

AC Timing Requirements

All test conditions: $V_{BAT} = 5.5 \text{ V to } 40 \text{ V}$, $R_L = 500 \Omega$, $T_A = -40^\circ\text{C to } 125^\circ\text{C}$, unless otherwise noted.

Parameter		Conditions	Min	Typ	Max	Unit
t_{RX_PD}	Receiver propagation delay	Rising and falling			6	μs
t_{RX_SYM}	Receiver propagation delay symmetry		-2		2	μs
$t_{WAKE_DOM_LIN}$	LIN dominant wake-up time	Sleep mode	30	80	150	μs
$t_{TO_DOM_TXD}$	TXD dominant time-out time	$V_{TXD} = 0 \text{ V}$	6	12	20	ms
t_{MODE}	Mode select time ⁽¹⁾		3		16	μs
t_{EN-TXD}	Delay time from EN to TXD ⁽¹⁾		0		1	μs
t_{DET_UVVCC}	Undervoltage detection time on VCC pin ⁽¹⁾		1	7.4	15	μs
t_{RST}	Reset time		2	4.3	8	ms

(1) The test data is based on bench test and design simulation.

Parameter Measurement Information

Test Circuit

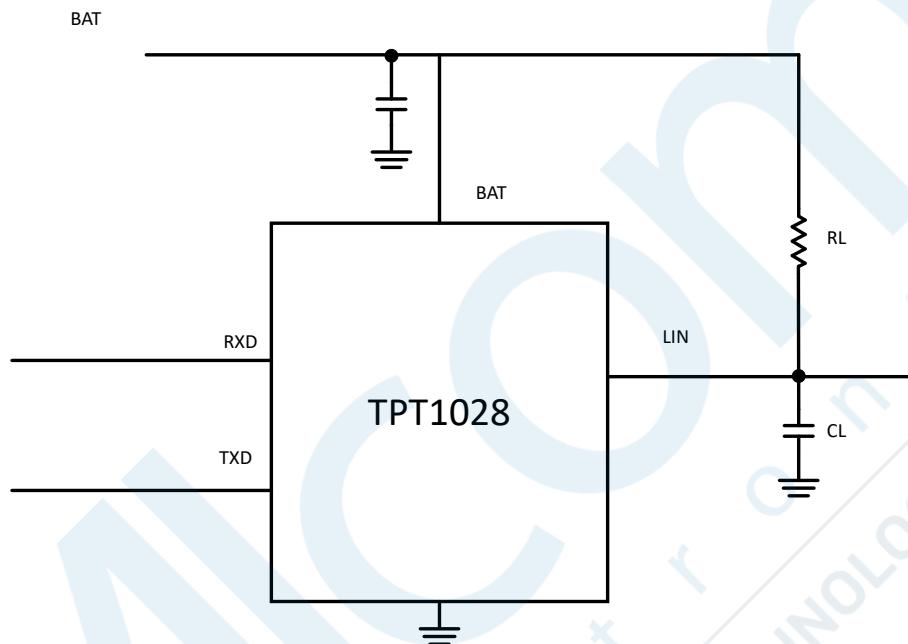


Figure 1. LIN Transceiver Timing Parameter Test Circuit

Parameter Diagram

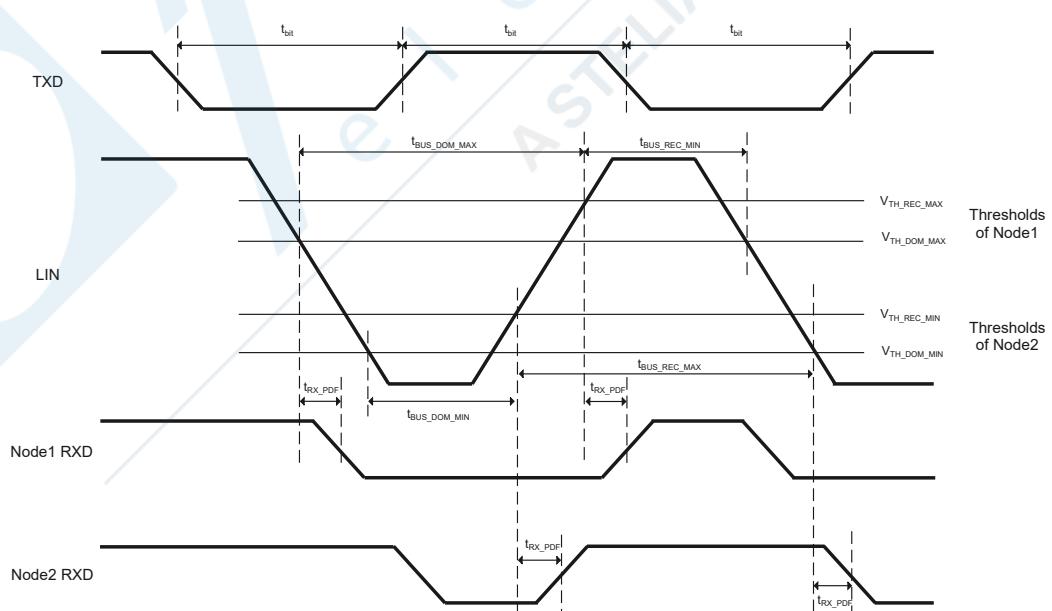
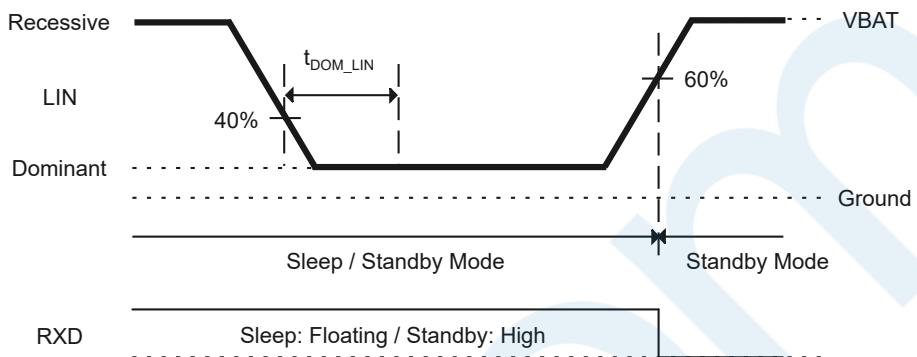


Figure 2. LIN Transceiver Timing Diagram

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)**Figure 3. Remote Wake-up Diagram**

Detailed Description

Overview

The TPT1028xQ is a local interconnect network (LIN) system basis chip (SBC), which includes a LIN transceiver, compliant to the ISO 17987-4, SAE J2602 and LIN 2.0, LIN 2.1, LIN 2.2, and LIN 2.2-A physical layer standard, and an integrated low drop out (LDO) voltage regulator. LIN is a low-speed Universal Asynchronous Receiver Transmitter (UART) communication protocol that supports automotive in-vehicle sub-networks. The LIN SBC is designed in LIN networks up to 20 Kbps and reduces system complexity by providing a 5-V or 3.3-V LDO to power the microprocessors, sensors, and other devices. The device supports Sleep mode, in which the LDO and LIN transceivers are shut down while still able to be waken-up via the LIN bus. The device integrates a pull high resistor for LIN slave applications and ESD protection which allows applications to operate with a reduced dependence on external components. With an optimized circuit design, the TPT1028xQ exhibits very low electromagnetic emission (EME) and high electromagnetic immunity (EMI) capabilities. As designed, the device features overvoltage and loss of ground protection from -45 V to +45 V, over-temperature shutdown, under voltage and short to ground protection, and other protection features to enhance the device and network robustness. The TPT1028xQ is available in SOP-8, ESOP-8, and DFN3X3-8 packages and is AEC-Q100 qualified for automotive applications.

Functional Block Diagram

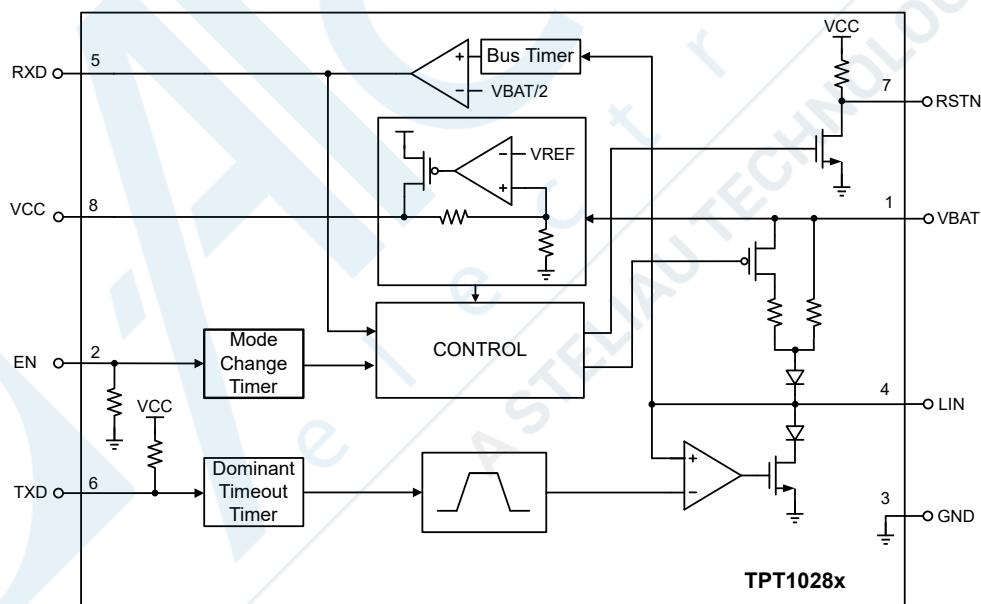


Figure 4. Functional Block Diagram

Feature Description

Device Operating Modes

The TPT1028xQ supports modes for Normal mode, Power-on mode, Standby mode, and Sleep mode. The figure below shows the state diagram.

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

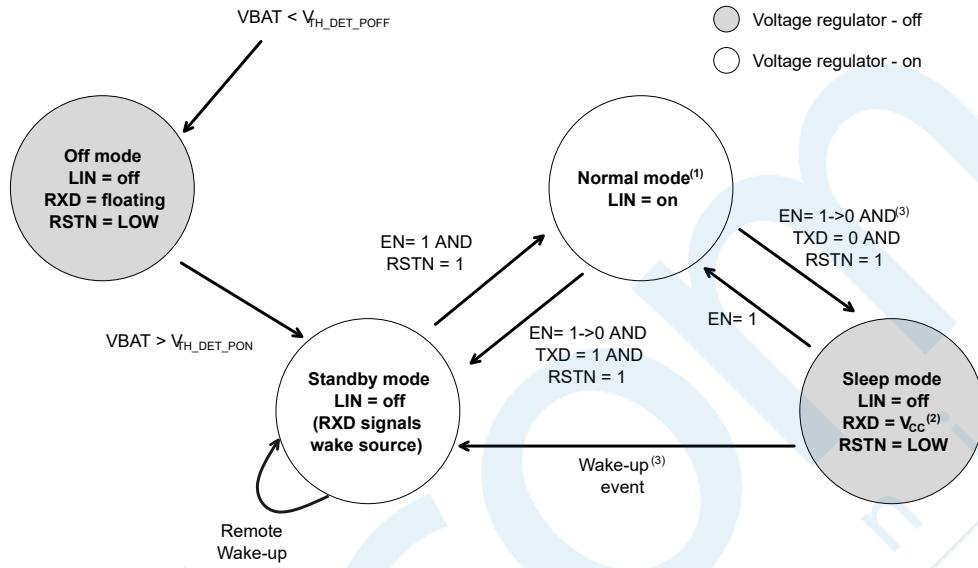


Figure 5. Functional Block Diagram

1. The LIN transmitter is enabled in Normal mode when EN and RST_N are high. If EN and/or RST_N go low, the LIN transmitter is disabled. The device can be remotely woken-up via the LIN bus.
2. Until V_{CC} drops below 2 V.
3. The device switches to Standby mode without initiating a reset if a wake-up event and a go-to-sleep event occur simultaneously.

Table 2. Function Table

Mode	EN	RXD	RST_N	Transmitter	LIN BUS Termination
Normal	High	High: recessive state Low: dominant state	V_{CC}	Normal	30 kΩ
Sleep	Low	Floating	GND	Off	Weak current pull-up
Standby	Low	Low (Remote wake-up)	V_{CC}	Off	30 kΩ
		High			
Off	/	Floating	GND	Off	Weak current pull-up

Off Mode

The device switches to Off mode if the battery supply voltage drops below the under-voltage protection threshold or the junction temperature exceeds the overtemperature protection activation threshold.

The LDO and LIN transceiver are disabled in Off mode, the RST_N pin keeps low.

Normal Mode

The device switches to Normal mode from Standby mode or Sleep mode if the EN pin is pulled high.

In Normal mode, the LDO is enabled, and the LIN transceiver can transmit and receive data through the LIN bus line. The receiver detects the data stream at the LIN bus input pin and transfers it to the microcontroller via the RXD pin. On the bus,

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

a HIGH level corresponds to a recessive state, while a LOW level represents a dominant state. The receiver incorporates a voltage-dependent threshold with hysteresis and an integrated filter to suppress noise on the bus.

The transmit data stream from the protocol controller at the TXD input is converted by the transmitter into a bus signal with an optimized slew rate and wave shaping, aiming to minimize electromagnetic emissions (EME). The LIN bus output pin is pulled HIGH through an internal slave termination resistor. For master applications, an external resistor in series with a diode should be connected between pin VBAT and pin LIN.

Standby Mode

Standby mode is a low-power mode for power-saving applications. The device switches to Standby mode from Off mode if the battery supply voltage rises above the power-on detection threshold.

The device switches to Standby mode from Normal mode if pin TXD is high and pin EN is low during the mode select window.

Standby mode is automatically activated whenever wake-up occurs while the device is in Sleep mode. The remote wake-up event is indicated by a low level on the RXD pin, which can serve as an interrupt for the microcontroller.

The LDO is enabled in Standby mode, and the LIN transceiver is disabled and is capable of being remote wake-up. The wake-up source is indicated by the level on RXD.

Sleep Mode

The Sleep mode offers an extremely low power mode that guarantees extremely low current consumption.

The device switches to Sleep mode from Normal mode if pin TXD and pin EN are both low during the mode select window. The LDO and LIN transceiver are disabled in Sleep mode and pin RST_N is forced low. The device is capable of being remote wake-up via the LIN bus. Input filters are incorporated at the receiver to prevent undesired wake-up events caused by automotive transients or electromagnetic interference (EMI).

Wake-up

A remote wake-up event triggers a transition to Standby mode from Sleep mode.

Remote wake-up through the LIN bus by transmitting a dominant bus state that is sustained for a duration of at least $t_{WAKE_DOM_LIN}$, then followed by a rising edge.

Power Supply

Battery Supply Input

The battery supply, V_{BAT} pin, operating range is from 5.5 V to 40 V, the maximum voltage device can handle is 45 V. If the V_{BAT} input voltage drops below V_{TH_DET_POFF}, the device switches to Off mode, the LDO and LIN transceiver is disabled. The device exits Off mode as soon as the battery supply voltage rises above the V_{TH_DET_PON}. An external diode is needed in series to protect the device against negative voltage.

Voltage Regulator Output

The device integrated a low-dropout voltage regulator supplied via V_{BAT} pin, the V_{CC} output current up to 100 mA. There are two output voltage versions for different power supply voltage microcontroller: the TPT10285 output voltage is 5 V, and the TPT10283 output voltage is 3.3 V.

Reset

The VCC voltage is monitored continuously; if VCC drops below V_{UV} for $t_{DET_UV_VCC}$, an undervoltage event is detected, and the RST_N pin sets low. When VCC exceeds the undervoltage recovery threshold V_{UVR} for T_{RST} , the RST_N pin goes back to high again.

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Protection Features

TXD Dominant Time-out

The device detects TXD dominant time-out and prevents a permanent low on the TXD pin driving the LIN bus into permanent dominant blocking the LIN bus network. If the TXD remains low for longer than t_{TXD_DTO} , the transmitter is disabled until the fault flag has been cleared.

Under-voltage Lockout (UVLO)

The device integrates under-voltage detection and lockout circuit of the supply terminal to keep the device in protected mode if the supply voltage drops below the threshold until the supply voltage is higher than the UVLO threshold. This protects the device and system during undervoltage events on supply terminals.

Over-Temperature Protection (OTP)

The device is protected against over-temperature conditions. If the virtual junction temperature exceeds the shutdown junction temperature T_{J_SD} , the device switches to Off mode. The voltage regulator and the LIN transmitter is switched off, and the pin RST_N is driven low. When the virtual junction temperature falls below $T_{J_SD_R}$, the device switches to normal mode.

Fail-safe Features

An internal pull-down to GND on the TXD pin to establish a predetermined level in case the TXD pin is disconnected.

RXD pin is set floating when the VBAT pin is unpowered.

The LIN transmitter is disabled when either EN or RST_N is low

LIN transmitter is only enabled if a recessive level is present on pin TXD after switching to Normal mode.

The current limit is applied to the LIN transmitter output to protect the LIN bus short circuits to VBAT or GND.

VBAT and GND loss does not impact the LIN bus or the MCU. No reverse current flows from the bus into the LIN pin. The internal integrated LIN slave termination resistor keeps the current path from VBAT to LIN. Disconnecting the LIN transceiver from the power supply does not affect the LIN bus.

Application and Implementation

Note

Information in the following application sections is not part of the 3PEAK's component specification and 3PEAK does not warrant its accuracy or completeness. 3PEAK's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

Typical Application

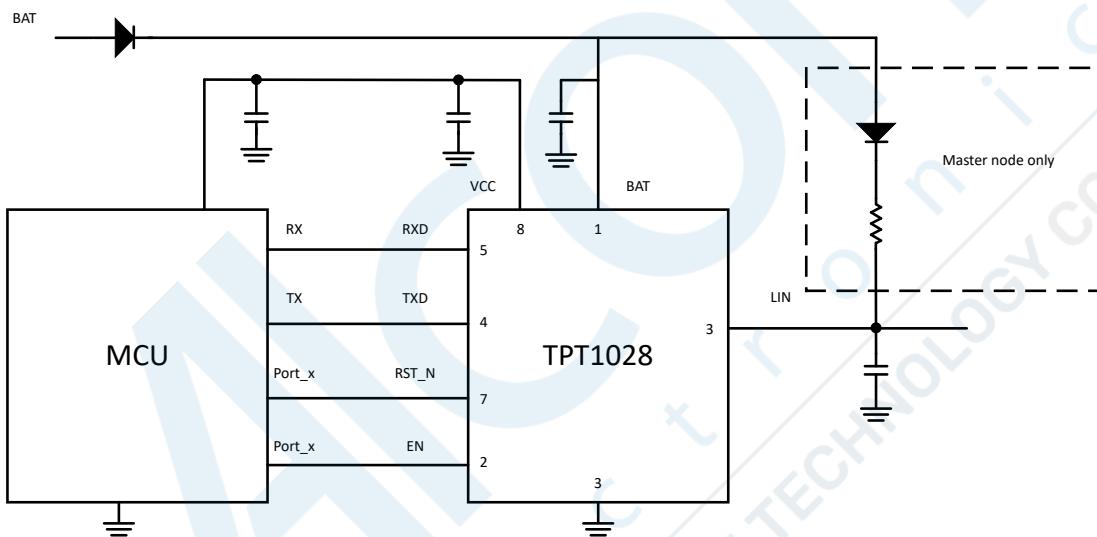
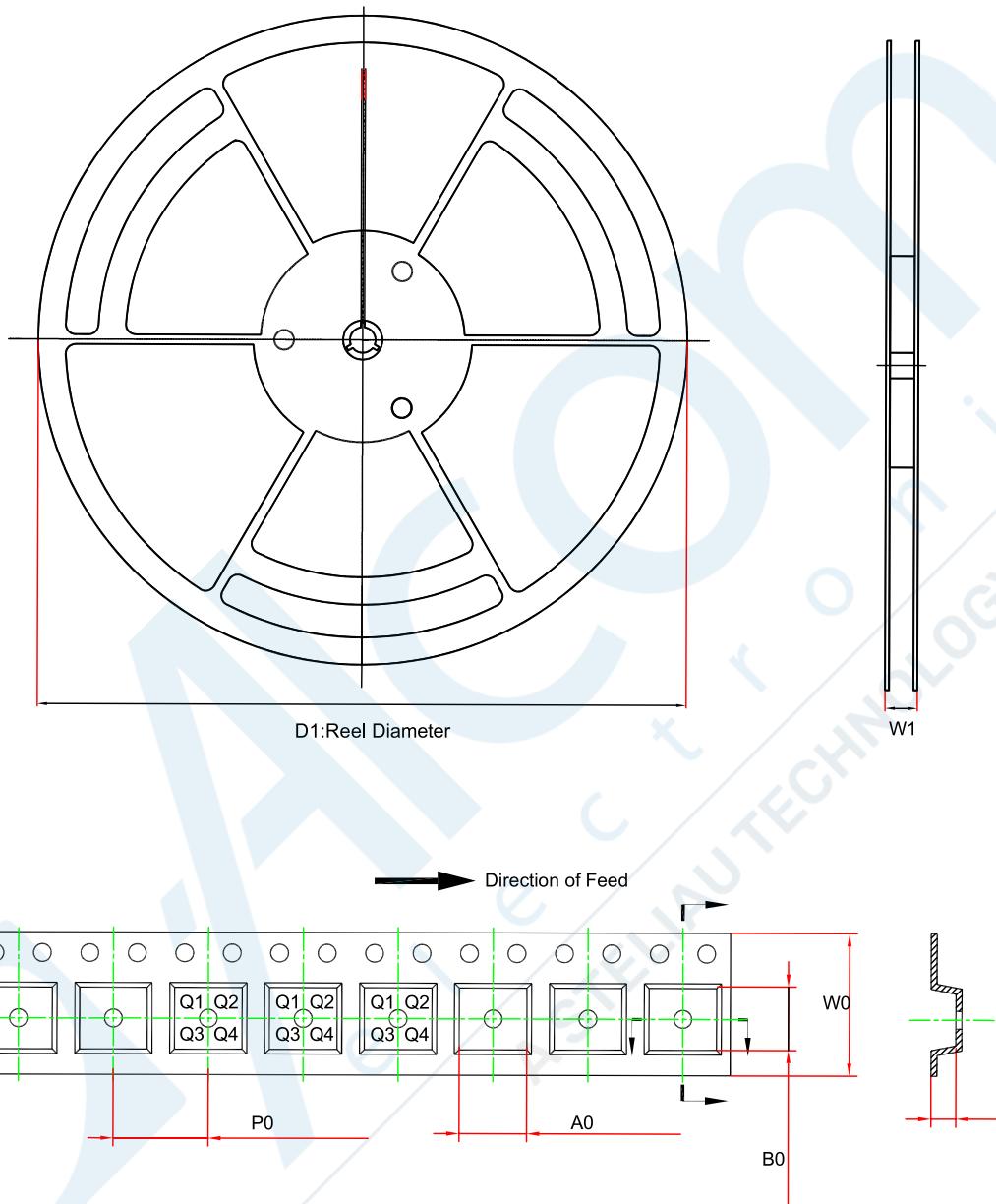


Figure 6. Typical Application Circuit

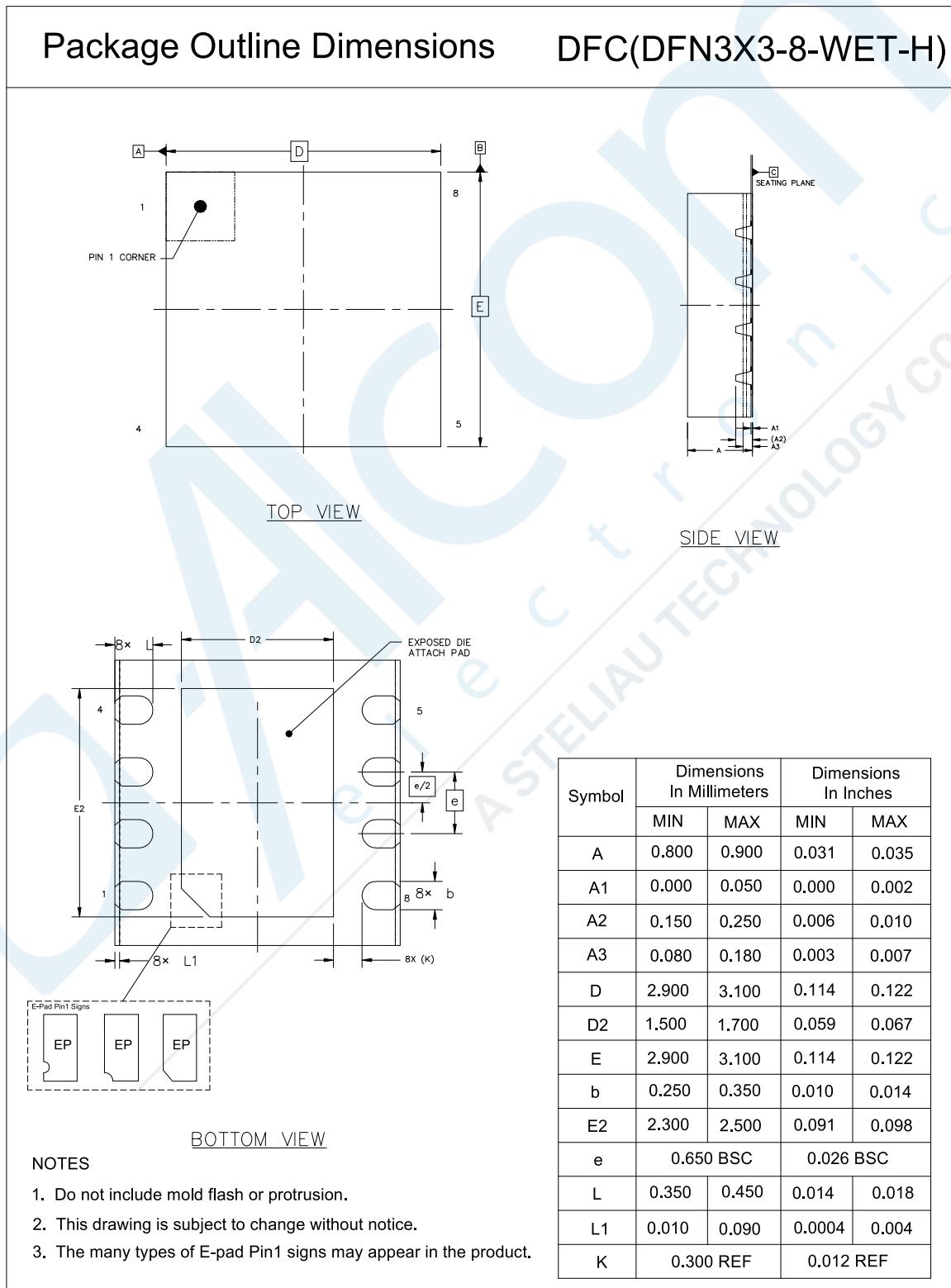
Tape and Reel Information



Order Number	Package	D1 (mm)	W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	W0 (mm)	Pin1 Quadrant
TPT10283Q-DFCR-S	DFN3X3-8	330	17.6	3.3	3.3	1.1	8	12	Q1
TPT10283Q-SO1R-S	SOP-8	330	17.6	6.5	5.4	2	8	12	Q1
TPT10283Q-ES1R-S	ESOP-8	330	17.6	6.4	5.4	2.1	8	12	Q1
TPT10285Q-DFCR-S	DFN3X3-8	330	17.6	3.3	3.3	1.1	8	12	Q1
TPT10285Q-SO1R-S	SOP-8	330	17.6	6.5	5.4	2	8	12	Q1
TPT10285Q-ES1R-S	ESOP-8	330	17.6	6.4	5.4	2.1	8	12	Q1

Package Outline Dimensions

DFN3X3-8



SOP8

Package Outline Dimensions		SO1(SOP-8-A)			
Symbol	Dimensions In Millimeters		Dimensions In Inches		
	MIN	MAX	MIN	MAX	
A	1.350	1.750	0.053	0.069	
A1	0.050	0.250	0.002	0.010	
A2	1.250	1.550	0.049	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.700	5.100	0.185	0.201	
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
e	1.270 BSC		0.050 BSC		
L	0.400	1.000	0.016	0.039	
θ	0	8°	0	8°	

NOTES

1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.

ESOP8

Package Outline Dimensions		ES1(ESOP-8-F)			
Symbol	Dimensions In Millimeters		Dimensions In Inches		
	MIN	MAX	MIN	MAX	
A	1.300	1.700	0.051	0.067	
A1	0.000	0.100	0.000	0.004	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.700	5.100	0.185	0.201	
D1	2.850	3.250	0.112	0.128	
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
E2	1.950	2.360	0.077	0.093	
e	1.270 BSC		0.050 BSC		
L	0.400	1.270	0.016	0.050	
θ	0	8°	0	8°	

NOTES

1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

Order Information

Order Number	Operating Temperature Range	Package	Marking Information	MSL	Transport Media, Quantity	Eco Plan
TPT10283Q-DFCR-S	-40 to 125°C	DFN3X3-8	T283Q	MSL1	Tape and Reel,4000	Green
TPT10283Q-SO1R-S	-40 to 125°C	SOP-8	T283Q	MSL1	Tape and Reel,4000	Green
TPT10283Q-ES1R-S	-40 to 125°C	ESOP-8	T283Q	MSL1	Tape and Reel,4000	Green
TPT10285Q-DFCR-S	-40 to 125°C	DFN3X3-8	T285Q	MSL1	Tape and Reel,4000	Green
TPT10285Q-SO1R-S	-40 to 125°C	SOP-8	T285Q	MSL1	Tape and Reel,4000	Green
TPT10285Q-ES1R-S	-40 to 125°C	ESOP-8	T285Q	MSL1	Tape and Reel,4000	Green

Green: 3PEAK defines "Green" to mean RoHS compatible and free of halogen substances.



TPT1028xQ

Automotive Fault Protected 125mA LIN System Basis Chip (SBC)

IMPORTANT NOTICE AND DISCLAIMER

Copyright® 3PEAK 2012-2025. All rights reserved.

Trademarks. Any of the 思瑞浦 or 3PEAK trade names, trademarks, graphic marks, and domain names contained in this document /material are the property of 3PEAK. You may NOT reproduce, modify, publish, transmit or distribute any Trademark without the prior written consent of 3PEAK.

Performance Information. Performance tests or performance range contained in this document/material are either results of design simulation or actual tests conducted under designated testing environment. Any variation in testing environment or simulation environment, including but not limited to testing method, testing process or testing temperature, may affect actual performance of the product.

Disclaimer. 3PEAK provides technical and reliability data (including data sheets), design resources (including reference designs), application or other design recommendations, networking tools, security information and other resources "As Is". 3PEAK makes no warranty as to the absence of defects, and makes no warranties of any kind, express or implied, including without limitation, implied warranties as to merchantability, fitness for a particular purpose or non-infringement of any third-party's intellectual property rights. Unless otherwise specified in writing, products supplied by 3PEAK are not designed to be used in any life-threatening scenarios, including critical medical applications, automotive safety-critical systems, aviation, aerospace, or any situations where failure could result in bodily harm, loss of life, or significant property damage. 3PEAK disclaims all liability for any such unauthorized use.